

Product Overview

SI3443DV: P-Channel 2.5V Specified PowerTrench® MOSFET -20V, -4A, 65mΩ

For complete documentation, see the data sheet.

This P-Channel 2.5V specified MOSFET is produced using Fairchild's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain low gate charge for superior switching performance. These devices have been designed to offer exceptional power dissipation in a very small footprint for applications where the larger packages are impractical.

Features

- -4 A, -20 V
- $R_{DS(ON)} = 0.065\Omega$ @ $V_{GS} = -4.5$ V
- $R_{DS(ON)} = 0.100\Omega$ @ $V_{GS} = -2.5$ V
- Fast switching speed
- Low gate charge (7.2nC typical)
- High performance trench technology for extremely low $R_{DS(ON)}$
- SuperSOT™ -6 package: small footprint (72% smaller than standard SO-8); low profile (1mm thick)

Applications

- This product is general usage and suitable for many different applications.

Part Electrical Specifications

Product	Compliance	Status	Chan- nel Polar- ity	Conf- ig- urati- on	V_{SS} Min (V)	V_{GS} Max (V)	$V_{GS(th)}$ Max (V)	I_D Max (A)	P_D Max (W)	$R_{DS(on)}$ Max @ $V_{GS} =$ 2.5 V (mΩ)	$R_{DS(on)}$ Max @ $V_{GS} =$ 4.5 V (mΩ)	$R_{DS(on)}$ Max @ $V_{GS} =$ 10 V (mΩ)	Q_g Typ @ $V_{GS} =$ 4.5 V (nC)	Q_g Typ @ $V_{GS} =$ 10 V (nC)	C_{iss} Typ (pF)	Pack- age Type
SI3443DV	Pb-free Halide free	Active	P- Chan- nel	Singl- e	-20	8	-1.5	-4	1.6	100	65	-	17	7.2	640	TSO T-23- 6

For more information please contact your local sales support at www.onsemi.com.

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